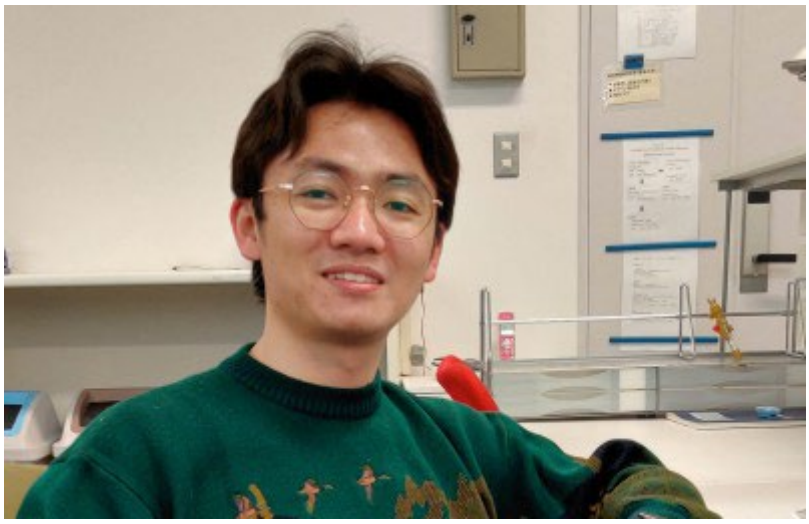
陳　斌杰 CHEN, Binjie

nclearlove(at)gmail.com



居室：北キャンパス電子科学研究所　3F 03-106
TEL : 011-706-9433 / FAX : 011-706-9432
研究キーワード：ルチル型酸化物の歪効果，マルチフェロイック

0000-0003-1838-2804

略歴

2020 年 4 月—現在　博士課程，北海道大学　大学院情報科学院（指導教員：太田裕道　教授，薄膜機能材料研究分野）

2019 年 10 月—2010 年 3 月　研究生，北海道大学　電子科学研究所（指導教員：太田裕道　教授，薄膜機能材料研究分野）

2018 年 10 月　—2019 年 8 月　　日本語訓練，中国赴日本国留学生予備学校

2015 年 9 月—2018 年 7 月　修士課程，Physical Electronics, East China Normal University

2011 年 9 月—2015 年 7 月　学士（工学），Materials Science and Engineering, Northwestern Polytechnical University

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